



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Features

- $BV_{CEO} > 100V$
- $I_C = 2A$ High Continuous Current
- $I_{CM} = 6A$ Peak Pulse Current
- Low Saturation Voltage $V_{CE(SAT)} < 300mV @ 1A$
- Complementary PNP Type: NK-FZT753

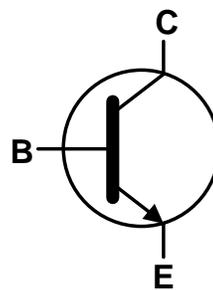
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208③
- Weight: 0.112 grams (Approximate)

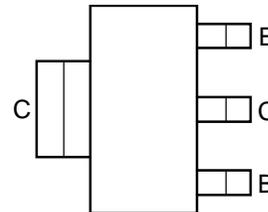
SOT223



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	2	A
Peak Pulse Current	I_{CM}	6	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

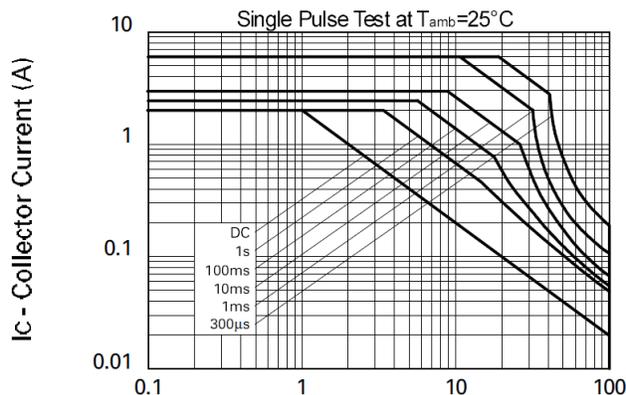
Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	(Note 5)	3
		(Note 6)	2
		(Note 7)	1.6
		(Note 8)	1.2
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	(Note 5)	41.7
		(Note 6)	62.5
		(Note 7)	78.1
		(Note 8)	104
Thermal Resistance Junction to Lead	$R_{\theta JL}$	12.9	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

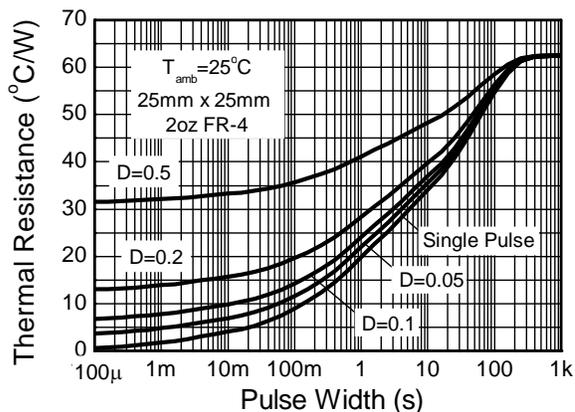
- Notes:
- For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 - Same as Note 5, except the device is mounted on minimum recommended pad layout.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

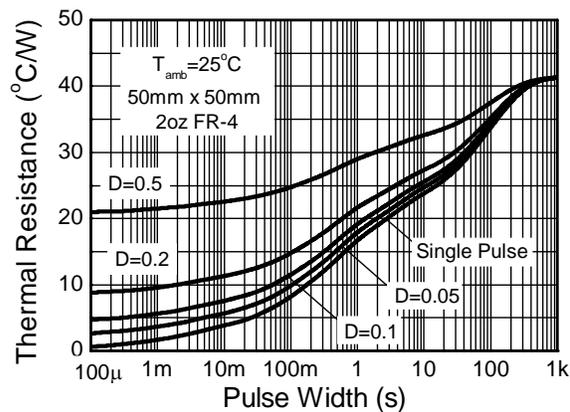


VCE - Collector Emitter Voltage (V)

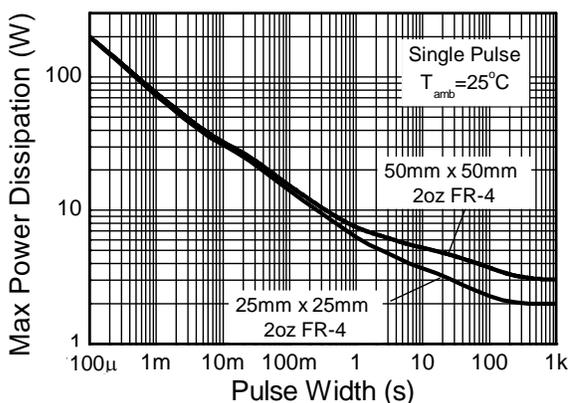
Safe Operating Area



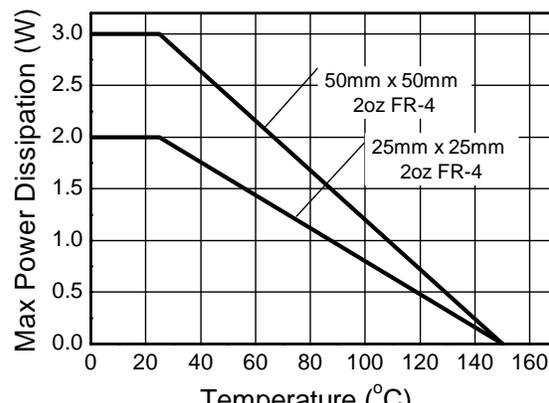
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



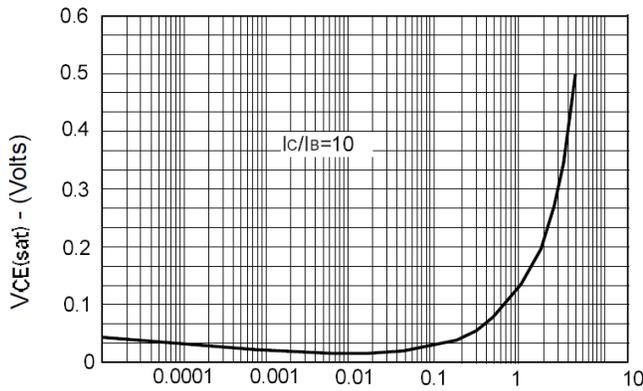
Derating Curve

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	120	–	–	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	100	–	–	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	–	–	V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	–	< 1	100	nA	V _{CB} = 100V
		–	–	10	μA	V _{CB} = 100V, T _A = +125°C
Emitter Cut-Off Current	I _{EBO}	–	< 1	100	nA	V _{EB} = 5.6V
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(SAT)}	–	0.13	0.3	V	I _C = 1A, I _B = 100mA
		–	0.23	0.5		I _C = 2A, I _B = 200mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(SAT)}	–	0.9	1.25	V	I _C = 1A, I _B = 100mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(ON)}	–	0.8	1.0	V	I _C = 1A, V _{CE} = 2V
DC Current Gain (Note 11)	h _{FE}	70	200	–	–	I _C = 50mA, V _{CE} = 2V
		100	200	300		I _C = 500mA, V _{CE} = 2V
		55	110	–		I _C = 1A, V _{CE} = 2V
		25	55	–		I _C = 2A, V _{CE} = 2V
Current Gain-Bandwidth Product	f _T	140	175	–	MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz
Switching Times	t _{ON}	–	80	–	ns	I _C = 500mA, V _{CC} = 10V, I _{B1} = -I _{B2} = 50mA
	t _{OFF}	–	1200	–		
Output Capacitance	C _{OBO}	–	–	30	pF	V _{CB} = 10V, f = 1MHz

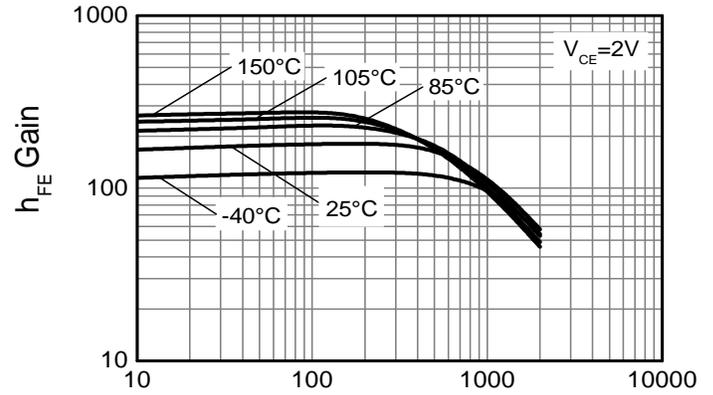
Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



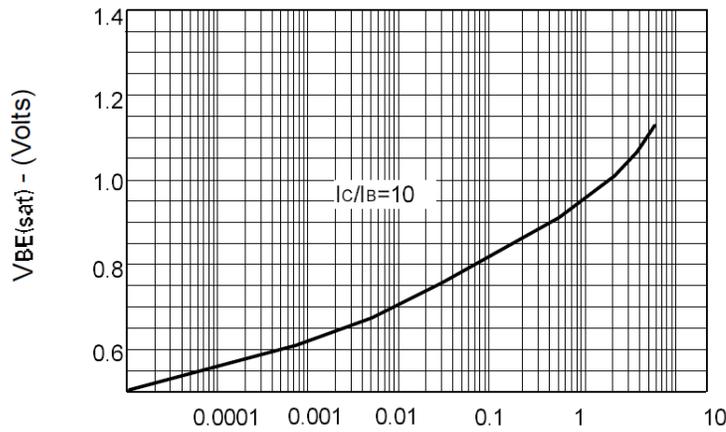
I_C - Collector Current (Amps)

$V_{CE(sat)}$ v I_C



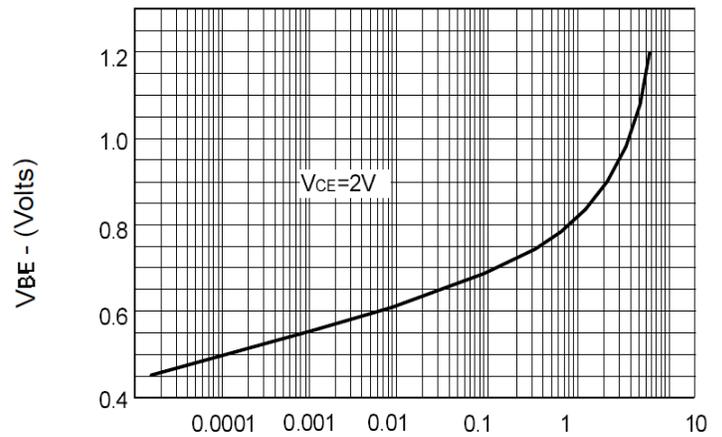
I_C - Collector Current (mA)

h_{FE} v I_C



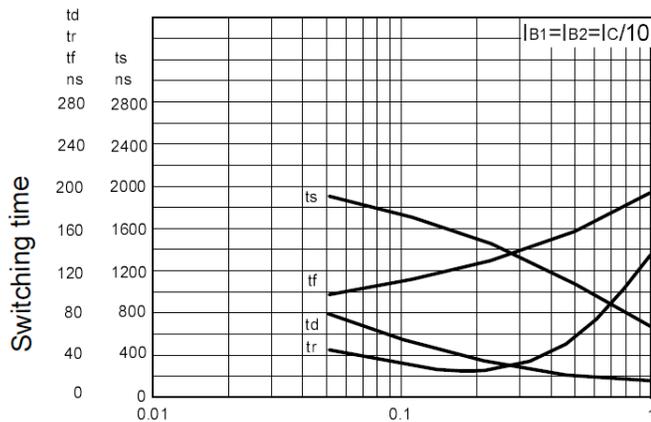
I_C - Collector Current (Amps)

$V_{BE(sat)}$ v I_C



I_C - Collector Current (Amps)

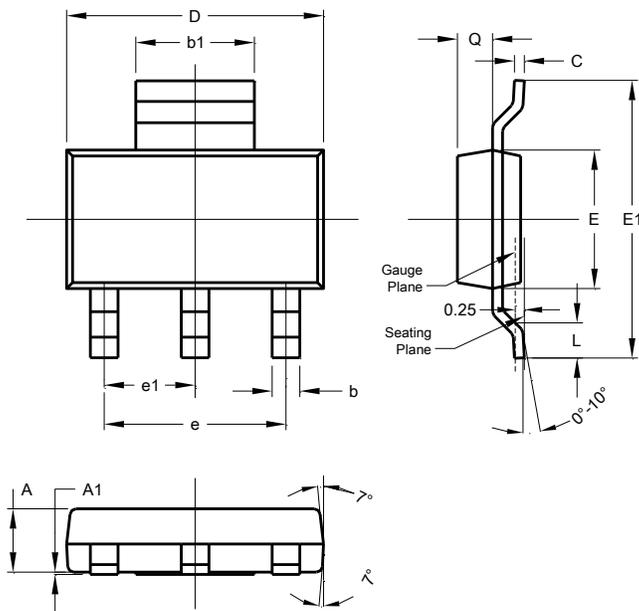
$V_{BE(on)}$ v I_C



I_C - Collector Current (Amps)

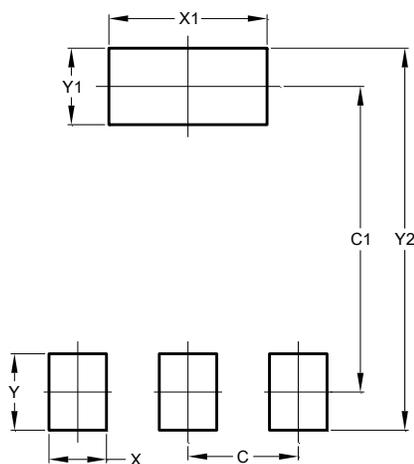
Switching Speeds

Package Outline Dimensions



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to voltage spacing between terminals.